

## Description

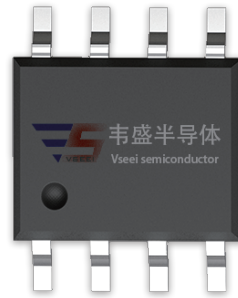
The VSM15P03 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ . This device is suitable for use as a load switch or in PWM applications.

## General Features

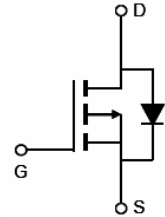
- $V_{DS} = -30V, I_D = -15A$   
 $R_{DS(ON)} < 12m\Omega @ V_{GS} = -10V$   
 $R_{DS(ON)} < 15m\Omega @ V_{GS} = -4.5V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

## Application

- PWM applications
- Load switch
- Uninterruptible power supply



SOP-8



Schematic Diagram

## Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VSM15P03-S8	VSM15P03	SOP-8	Ø330mm	12mm	4000 units

## Absolute Maximum Ratings ( $T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	-15	A
Drain Current-Pulsed <sup>(Note 1)</sup>	$I_{DM}$	-80	A
Maximum Power Dissipation	$P_D$	3.1	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ C$

## Thermal Characteristic

Thermal Resistance, Junction-to-Ambient <sup>(Note 2)</sup>	$R_{\theta JA}$	40	$^\circ C/W$
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## Electrical Characteristics ( $T_A = 25^\circ C$ unless otherwise noted)

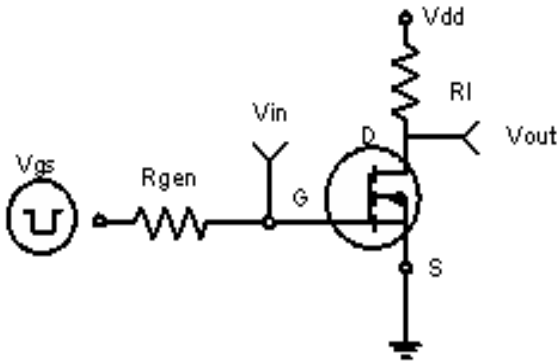
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-30	-33	-	V

Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V	-	-	-1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-0.8	-1.25	-2.2	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-15A	-	8.5	12	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-10A	-	11.5	15	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =-5V, I <sub>D</sub> =-15A	30	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, F=1.0MHz	-	2900	-	PF
Output Capacitance	C <sub>oss</sub>		-	410	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	280	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-15V, I <sub>D</sub> =-10A, V <sub>GS</sub> =-10V, R <sub>GEN</sub> =3Ω	-	15	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	11	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	44	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	21	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-15V, I <sub>D</sub> =-10A, V <sub>GS</sub> =-10V	-	48	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	12	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	14	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-2A	-	-	-1.2	V

## Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

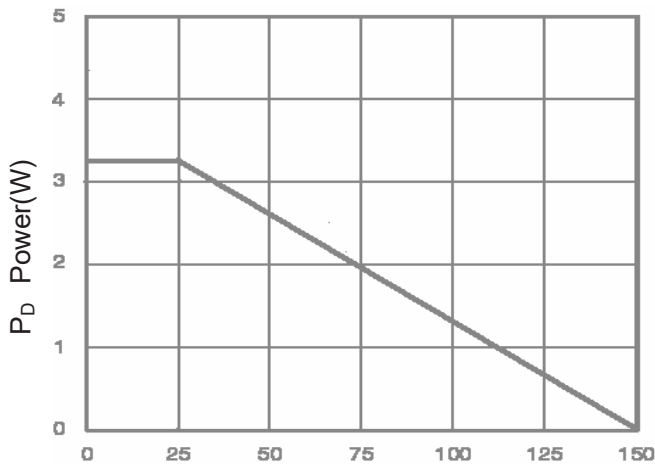
## Typical Electrical and Thermal Characteristics



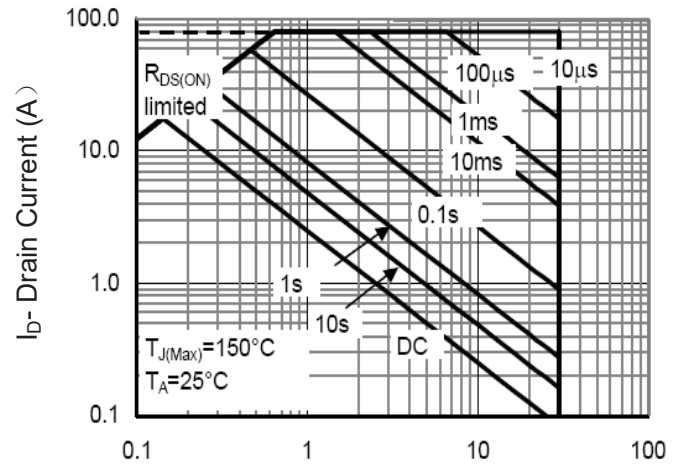
**Figure 1 Switching Test Circuit**



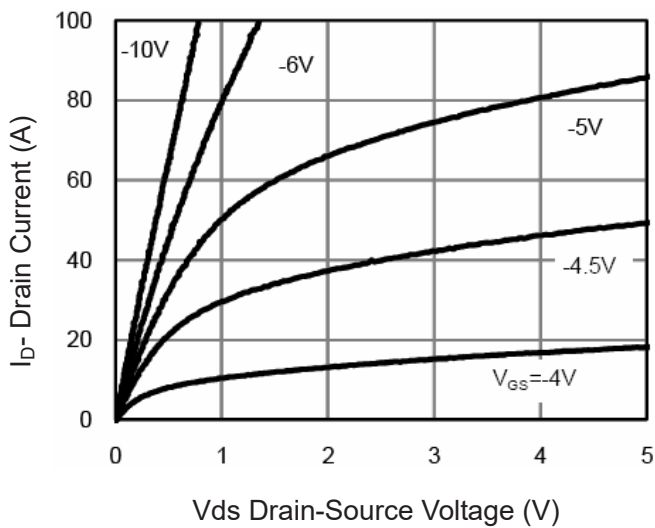
**Figure 2 Switching Waveforms**



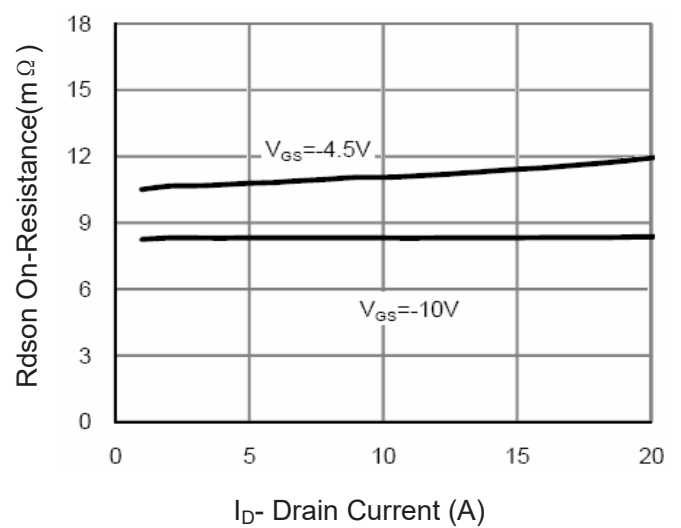
**Figure 3 Power Dissipation**



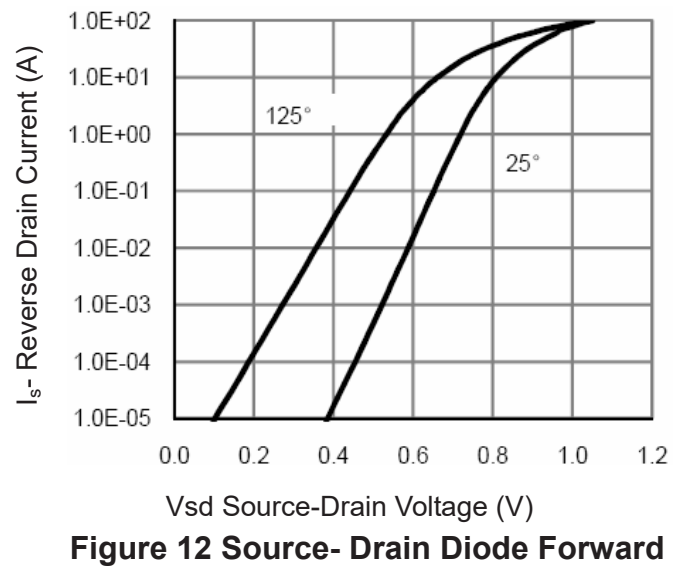
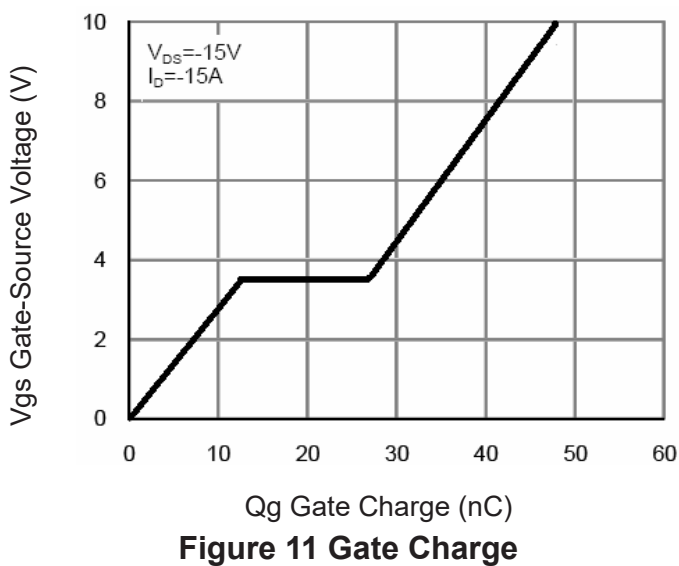
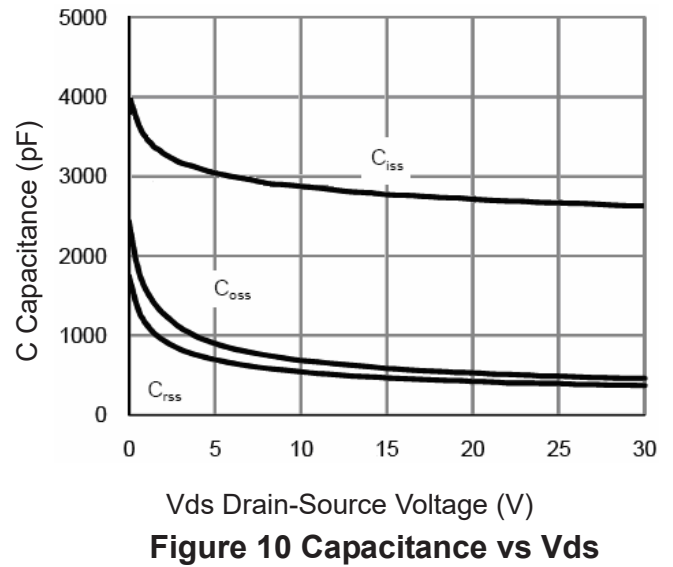
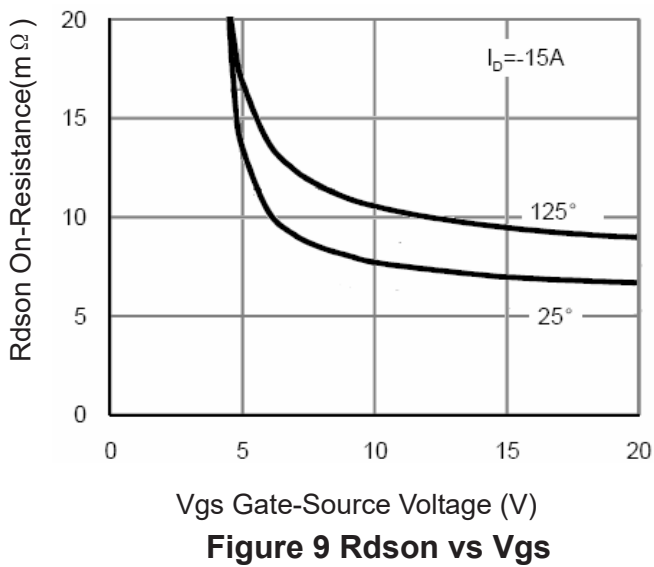
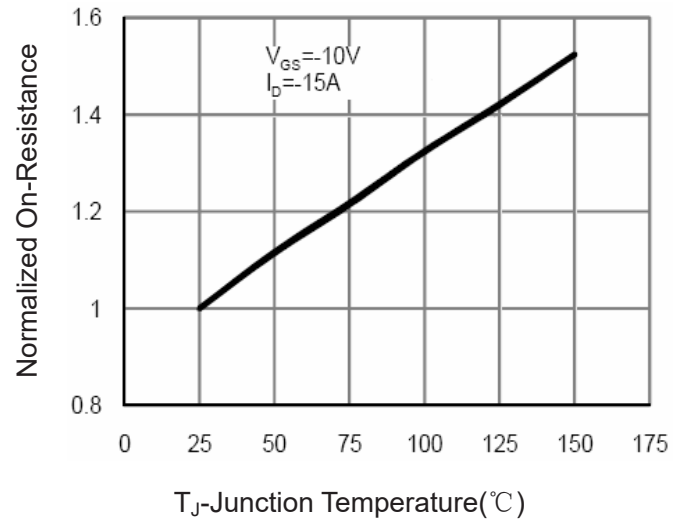
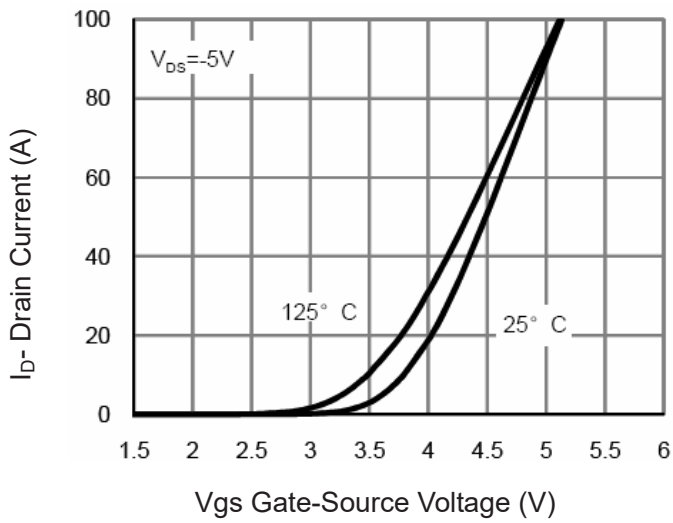
**Figure 4 Safe Operation Area**

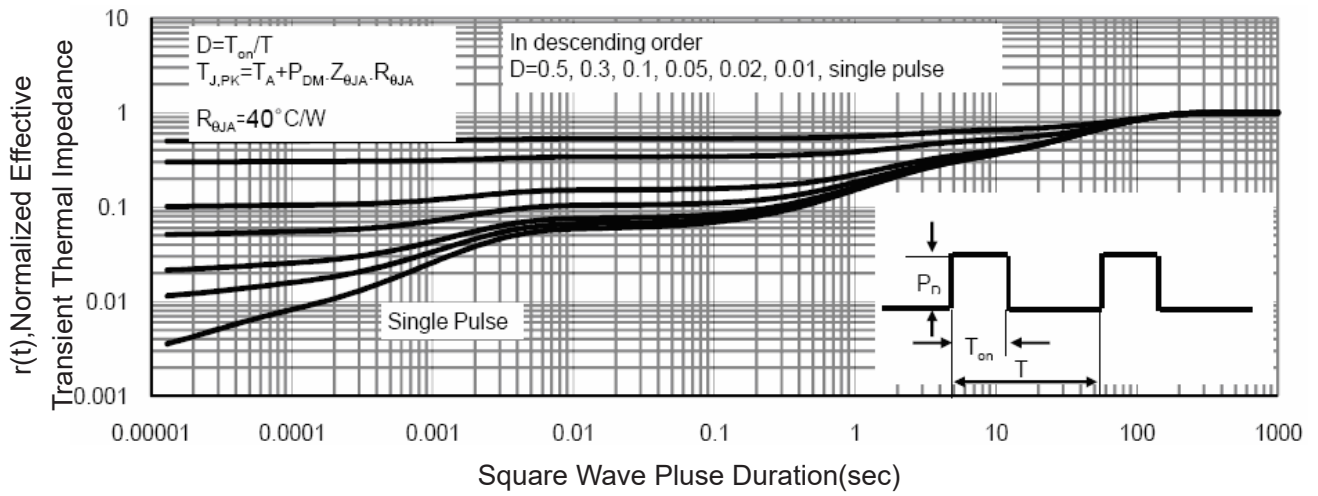


**Figure 5 Output Characteristics**



**Figure 6 Drain-Source On-Resistance**





**Figure 13 Normalized Maximum Transient Thermal Impedance**